

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No.:	7,427,555	Docket:	G&C 30794.94-US-WO
Issue Date:	September 23, 2008	Patentee:	Benjamin A. Haskell et al.
Title:	GROWTH OF PLANAR, NON-POLAR GALLIUM NITRIDE BY HYDRIDE VAPOR PHASE EPITAXY		

REQUEST FOR CERTIFICATE OF CORRECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

It is requested that a Certificate of Correction be issued correcting printing errors appearing in the above-identified United States patent. Two copies of the text of the Certificate in the suggested form are enclosed.

☐ As some of the errors listed are due to Applicants' mistake, our check in the amount of \$_____ is enclosed to cover the Certificate fee.

☒ As none of the errors listed is due to Applicants' mistake, no fee is necessary in connection with this Certificate.

Issuance of the Certificate of Correction would neither expand nor contract the scope of the claims, and re-examination is not required.

Please charge any additional fees or credit any overpayment to Deposit Account

No. 50-0494 of Gates & Cooper LLP.

Respectfully submitted,

Benjamin A. Haskell et al.
By their attorneys,

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Date: September 2, 2010

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